

MA2J111 (MA111)

TY epitaxial planar type

For switching circuits

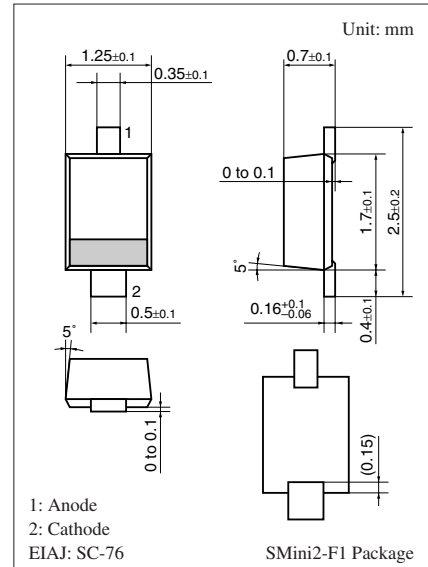
■ Features

- Allowing high-density mounting
- Short reverse recovery time t_{rr}
- Small terminal capacitance C_t
- High breakdown voltage: $V_R = 80$ V

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Reverse voltage	V_R	80	V
Maximum peak reverse voltage	V_{RM}	80	V
Forward current	I_F	100	mA
Peak forward current	I_{FM}	225	mA
Non-repetitive peak forward surge current *	I_{FSM}	500	mA
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

Note) *: $t = 1$ s



Marking Symbol: 1B

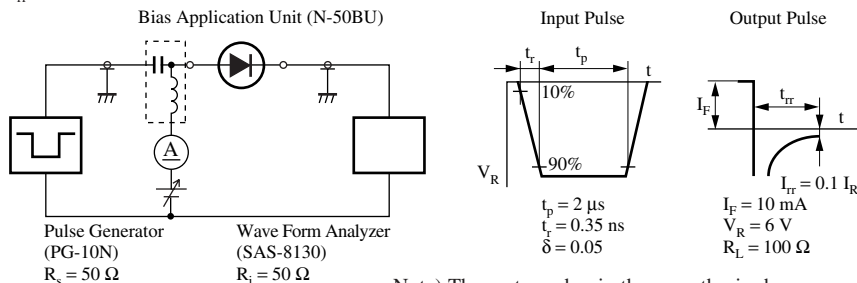
■ Electrical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Forward voltage	V_F	$I_F = 100$ mA		0.95	1.20	V
Reverse voltage	V_R	$I_R = 100$ μA	80			V
Reverse current	I_R	$V_R = 75$ V			100	nA
Terminal capacitance	C_t	$V_R = 0$ V, $f = 1$ MHz		0.6	1.2	pF
Reverse recovery time *	t_{rr}	$I_F = 10$ mA, $V_R = 6$ V $I_{rr} = 0.1 I_R$, $R_L = 100$ Ω			3	ns

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7031 measuring methods for diodes.

2. Absolute frequency of input and output is 100 MHz.

3. *: t_{rr} measurement circuit



Note) The part number in the parenthesis shows conventional part number.